

Silicon NPN Power Transistors

2SC3320

DESCRIPTION

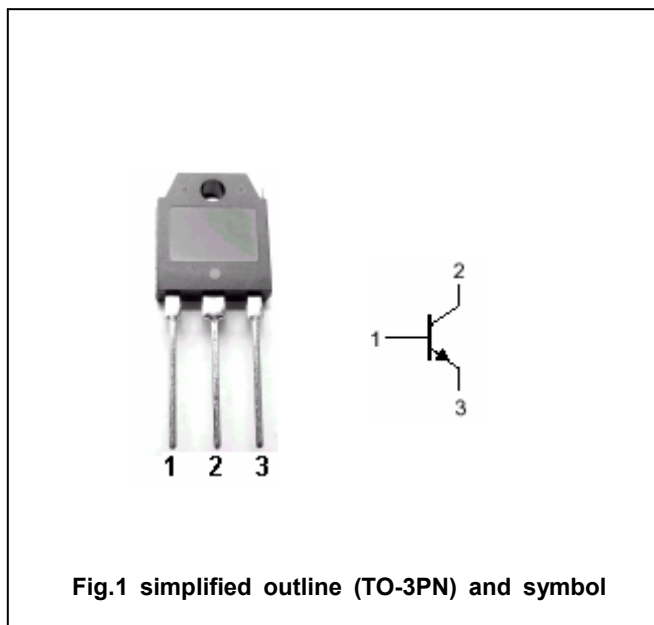
- With TO-3PN package
- High voltage ,high speed switching
- High reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		15	A
I_B	Base current		5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	80	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th(j-c)}$	Thermal resistance from junction to case	1.56	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; I_B=0$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A ; I_B=1.2A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A ; I_B=1.2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V ; I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V ; I_C=0$			1.0	mA
h_{FE}	DC current gain	$I_C=6A ; V_{CE}=5V$	10			

Switching times resistive load

t_{on}	Turn-on time	$I_C=7.5A ; I_{B1}=1.5A$ $I_{B2}=-3A ; R_L=20\Omega$ $P_W=20\mu s ; \text{Duty} < 2\%$			0.5	μs
t_s	Storage time				1.5	μs
t_f	Fall time				0.15	μs

Technical drawing of a mechanical part showing front, side, and top views with dimensions.

Front View Dimensions:

- Overall width: 15.60
- Inner width: 13.50
- Top width: 10.00
- Inner top width: 8.00
- Top hole diameter: $30\text{-}\phi 1.50$
- Inner top hole diameter: $10\text{-}\phi 3.50$
- Top hole radius: $R0.50$
- Top hole width: 12.00
- Top hole depth: 0.60
- Top hole diameter: $10\text{-}\phi 2.05\text{ }^{0}_{-0.05}$
- Top hole radius: $R0.50$
- Top hole width: 3.25
- Top hole depth: 2.00
- Top hole diameter: 0.00
- Top hole radius: 2.00

Side View Dimensions:

- Overall height: 40.10
- Top hole diameter: $\phi 5.50$
- Top hole width: 13.50
- Top hole depth: 7.00
- Top hole radius: $R0.50$
- Top hole width: 3.00
- Top hole depth: 2.00
- Top hole diameter: $10\text{-}\phi 2.05\text{ }^{0}_{-0.05}$
- Top hole radius: $R0.50$
- Top hole width: 3.25
- Top hole depth: 2.00
- Top hole diameter: 0.00
- Top hole radius: 2.00

Top View Dimensions:

- Overall width: 15.60
- Inner width: 13.50
- Top width: 10.00
- Inner top width: 8.00
- Top hole diameter: $30\text{-}\phi 1.50$
- Inner top hole diameter: $10\text{-}\phi 3.50$
- Top hole radius: $R0.50$
- Top hole width: 12.00
- Top hole depth: 0.60
- Top hole diameter: $10\text{-}\phi 2.05\text{ }^{0}_{-0.05}$
- Top hole radius: $R0.50$
- Top hole width: 3.25
- Top hole depth: 2.00
- Top hole diameter: 0.00
- Top hole radius: 2.00

Fig.2 outline dimensions(unindicated tolerance:±0.10 mm)

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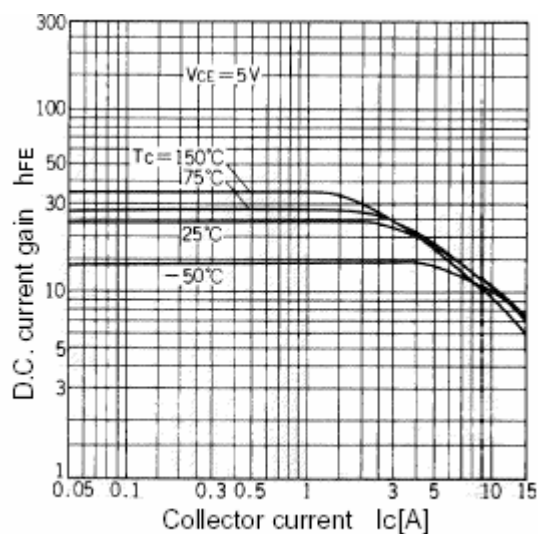


Fig.3 DC current Gain

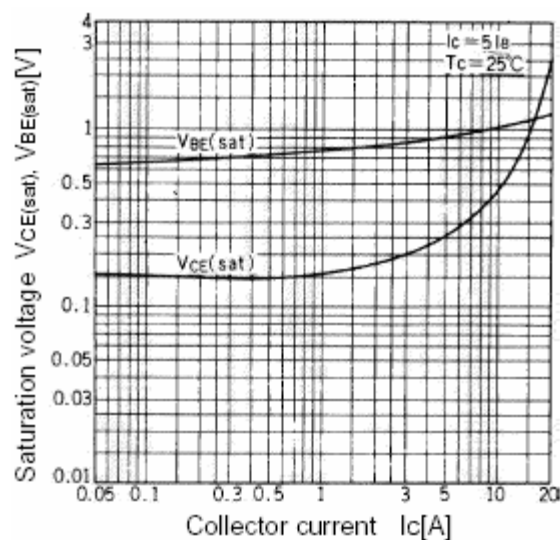
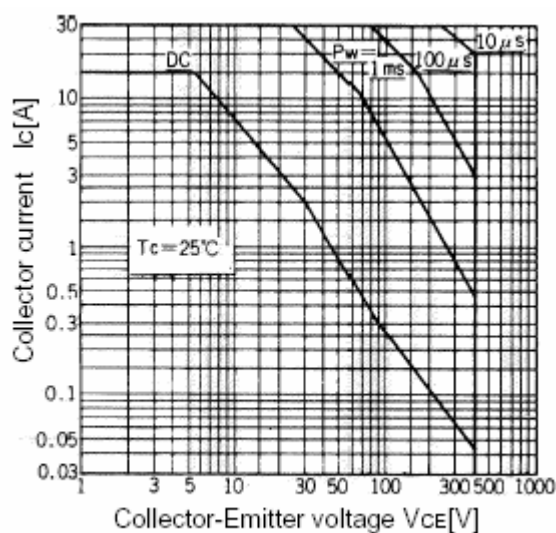
Fig.4 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

Fig.5 Safe Operating Area